

**Silicon NPN Power Transistors**

**2SD2025**

**DESCRIPTION**

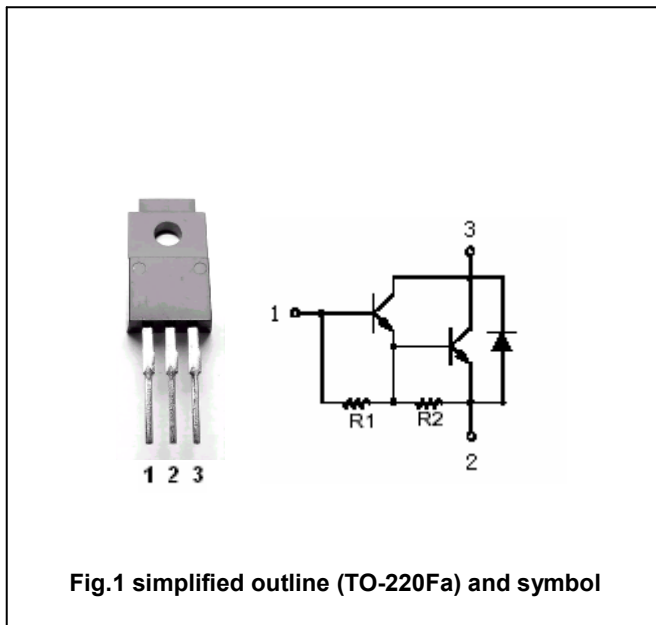
- With TO-220Fa package
- High DC current gain
- Low saturation voltage
- DARLINGTON
- Complement to type 2SB1344

**APPLICATIONS**

- For low frequency power amplifier and power driver applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Absolute maximum ratings(Ta=25℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	100	V
V <sub>CEO</sub>	Collector -emitter voltage	Open base	100	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		8	A
I <sub>CM</sub>	Collector current-peak		10	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25℃	2	W
		T <sub>C</sub> =25℃	30	
T <sub>j</sub>	Junction temperature		150	℃
T <sub>stg</sub>	Storage temperature		-55~150	℃

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =5mA; I <sub>B</sub> =0	100			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =50μA; I <sub>E</sub> =0	100			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =6mA			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			3.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2A; V <sub>CE</sub> =3V	1000		20000	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.2A; V <sub>CE</sub> =5V		40		MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1MHz		50		pF

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PACKAGE OUTLINE

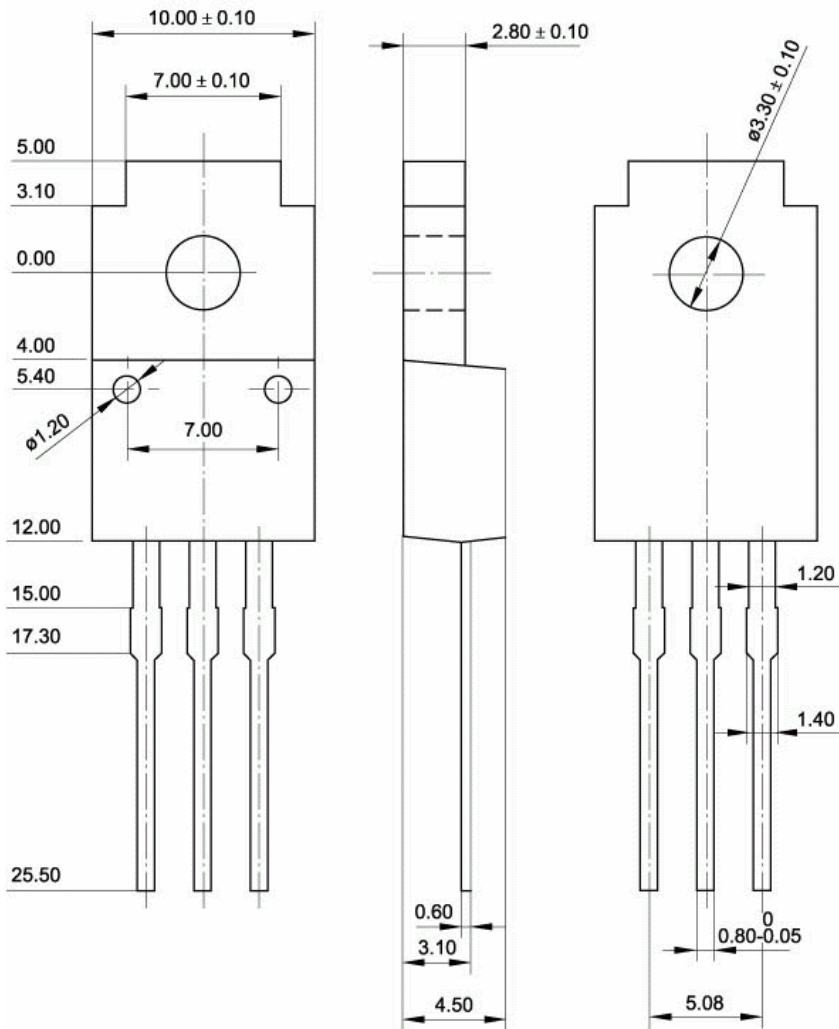


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)